

General Description

The HT7202 use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness.

General Features

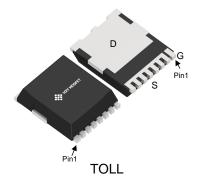
V_{DS} = 80V I_D = 400A

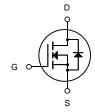
 $R_{DS(ON)}$ < 2m Ω @ V_{GS} =10V

Applications

Battery Protection

Power Distribution





N-Channel MOSFET

Package Marking and Ordering Information

Product ID		Pack	Marking	Qty(PCS)	
	HT7202	TOLL	400N08	2000	

Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit		
Drain-Source Voltage	V _{DS}	80	V		
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Praise Current	Tc=25°C		400		
Continuous Drain Current	T _C =100°C	l _D	253	A	
Pulsed Drain Current ¹	I _{DM}	1600	А		
Single Pulse Avalanche Energy ²	EAS	1280	mJ		
Total Power Dissipation T _C =25°C		P _D	468.8	W	
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to 175	°C		
Thermal Resistance from Junction-to-Ambient	Rеја	39	°C/W		
Thermal Resistance from Junction-to-Case	R _θ Jc	0.32	°C/W		



Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250µA	80	-	-	V
Gate-body Leakage current		Igss	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain	T _J =25°C	lana	V _{DS} = 80V, V _{GS} = 0V	-	-	1	μA
Current	T _J =100°C	IDSS	VDS = 80V, VGS = 0V	-	-	100	
Gate-Threshold Voltage		V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2	3	4	V
Drain-Source on-Resistance	e ⁴	R _{DS(on)}	V _{GS} = 10V, I _D = 20A	-	1.6	2	mΩ
Forward Transconductance	4	G fs	V _{DS} = 10V, I _D =20A	-	70	-	S
Dynamic Characteristic	S ⁵						
Input Capacitance		C _{iss}		-	8980	-	pF
Output Capacitance		Coss	V _{DS} = 40V, V _{GS} =0V, f =1MHz	-	1560	-	
Reverse Transfer Capacitance		Crss		-	90	-	
Gate Resistance		Rg	f=1MHz	-	2.4	-	Ω
Switching Characteristi	Switching Characteristics ⁵						
Total Gate Charge		Qg		-	140	-	nC
Gate-Source Charge		Qgs	$V_{GS} = 10V, V_{DS} = 40V,$ $I_{D} = 20A$	-	37.5	-	
Gate-Drain Charge		Q _{gd}		-	37.5	-	
Turn-on Delay Time		t _{d(on)}		-	27.5	-	ns
Rise Time		tr	$V_{GS} = 10V, V_{DD} = 40V,$	-	82	-	
Turn-off Delay Time		t _{d(off)}	$R_G = 3\Omega$, $I_D = 20A$	-	85	-	
Fall Time		t _f		-	52	-	
Body Diode Reverse Recovery Time		t _{rr}	1 004 11/14 4004/	-	98	-	ns
Body Diode Reverse Recov	ery Charge	Qrr	- I _F =20A, di/dt = 100A/μs	-	166	-	nC
Drain-Source Body Dio	Drain-Source Body Diode Characteristics						
Diode Forward Voltage ⁴		V _{SD}	I _S = 20A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	T _C =25°C	Is	-	-	-	400	Α

Notes:

- 1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C.
- 2. The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V, L=0.5mH, I_{AS} =50A.
- 3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
- 4. The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%.
- 5. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

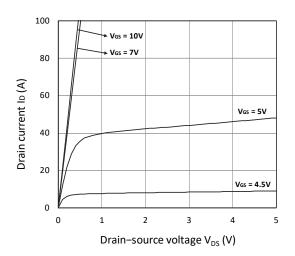


Figure 1. Output Characteristics

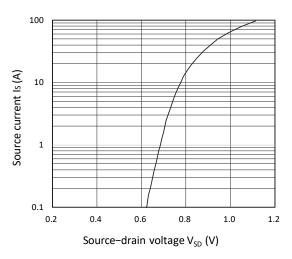


Figure 3. Forward Characteristics of Reverse

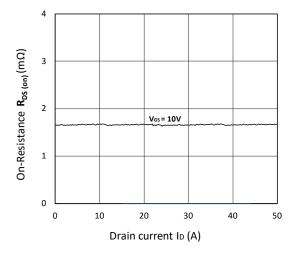


Figure 5. $R_{DS(ON)}$ vs. I_D

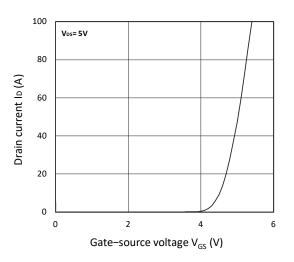


Figure 2. Transfer Characteristics

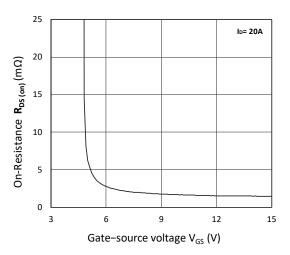


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

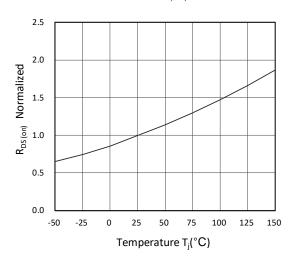


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

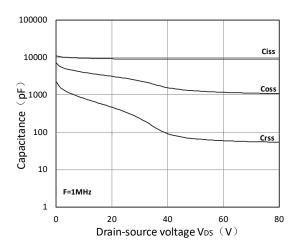


Figure 7. Capacitance Characteristics

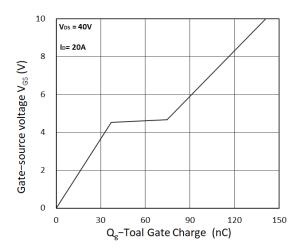


Figure 8. Gate Charge Characteristics

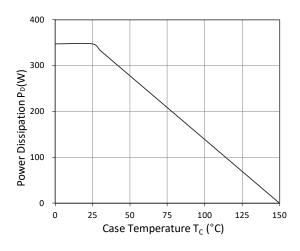


Figure 9. Power Dissipation

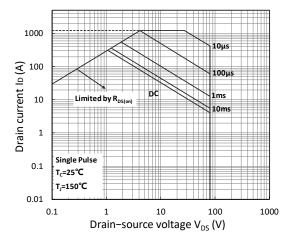


Figure 10. Safe Operating Area

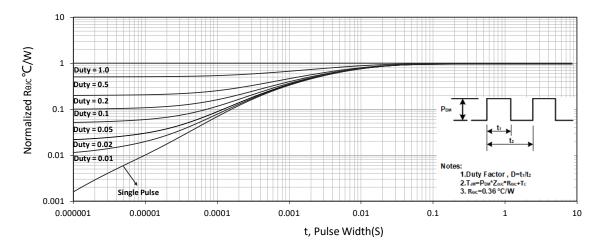
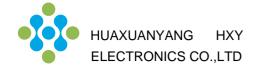


Figure 11. Normalized Maximum Transient Thermal Impedance



Test Circuit

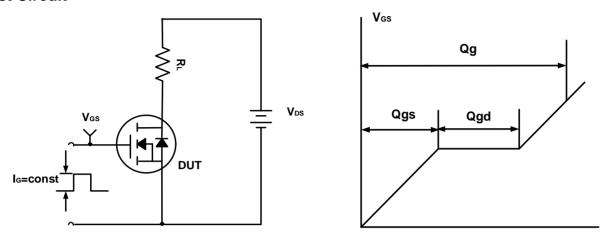


Figure A. Gate Charge Test Circuit & Waveforms

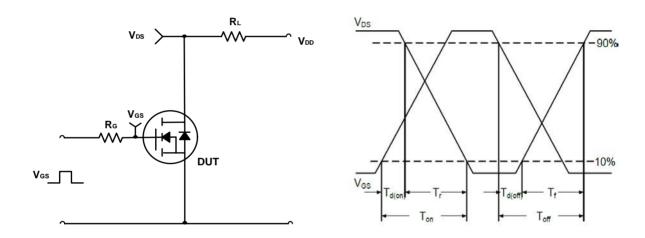


Figure B. Switching Test Circuit & Waveforms

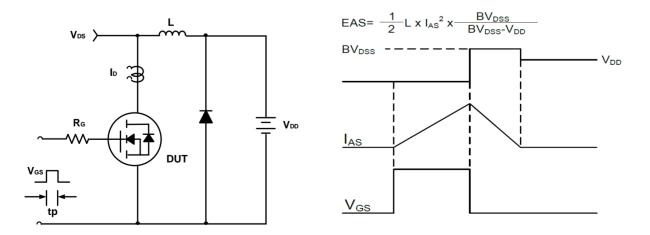
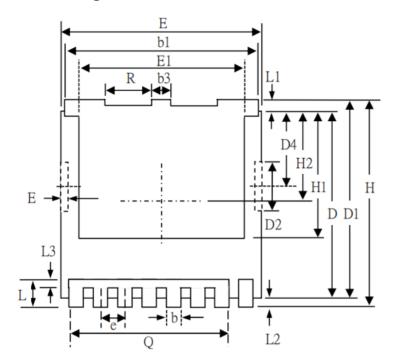


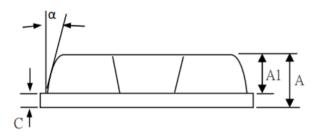
Figure C. Unclamped Inductive Switching Circuit & Waveforms



TOLL Package Information



R	A	CI	KS1	D	ΕV	VΤ	ΕW	V
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LAII	Dime	nsion	Are	In N	VI I I I	limeters.

2. Dimension Does Not Include Mold Protrusions.

Coursels al	mm			
Symbol	Min	Max		
А	2.20	2.40		
b	0.60	0.90		
b1	9.70	9.90		
С	0.40	0.60		
D	10.20	10.60		
D1	3.10	3.50		
D2	4.45	4.75		
Е	9.70	10.10		
E1	7.80	BSC		
E2	0.50	0.70		
е	1.200	BSC		
Н	11.45	11.90		
H1	6.75	5 BSC		
K	3.10	REF		
L	1.70	2.10		
L1	0.60	0.80		
L2	0.50	0.70		
θ	10° REF			

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